

Q2 6. (Amended) A tunnel magnetoresistive effective element as defined in claim 4, wherein the first leading electrode portion and the second leading electrode portion are provided in respective different sides from the center line of the ferromagnetic tunnel effective film.

7. (Amended) A tunnel magnetoresistive effective element as defined in claim 4, wherein the first leading electrode portion and the second leading electrode portion are provided in either side from the center line of the ferromagnetic tunnel effective film.

8. (Amended) A tunnel magnetoresistive effective element as defined in claim 6, wherein a planer angle of a line segment to a first center point of a boundary line between the first electrode/magnetic shielding portion and the first leading electrode portion from a center point of the ferromagnetic tunnel effective film for the bias magnetic field direction or a planer angle of a line segment to a second center point of a boundary line between the second electrode/magnetic shielding portion and the second leading electrode portion from the center point of the ferromagnetic tunnel effective film for the bias magnetic field direction is set to 5 degrees or over.

a3 9. (Amended) A tunnel magnetoresistive effective element as defined in claim 1, wherein the magnetic bias means includes a bias magnetic field-inductive layer to apply a given bias magnetic field to the free layer of the ferromagnetic tunnel effective film and a magnetic bias applying means to apply a given magnetic field to the bias magnetic field-inductive layer.

a4 12. (Amended) A thin film magnetic head comprising at least one reading element composed of a tunnel magnetoresistive effective element as defined claim 1.

a5 16. (Amended) A magnetic head device comprising a thin film magnetic head as defined in claim 12 and a head supporting device to support the thin film magnetic head.